

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C (Note 9)
60V	8mΩ @ V _{GS} = 10V	80A
	12mΩ @ V _{GS} = 4.5V	79A

Description and Applications

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R_{DS(ON)} and yet maintain superior switching performance. This device is ideal for use in Notebook battery power management and Loadswitch.

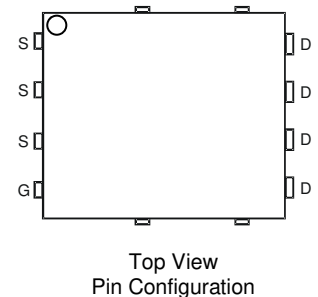
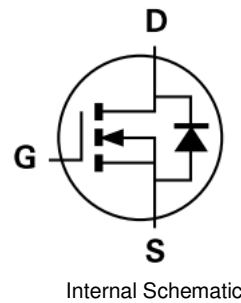
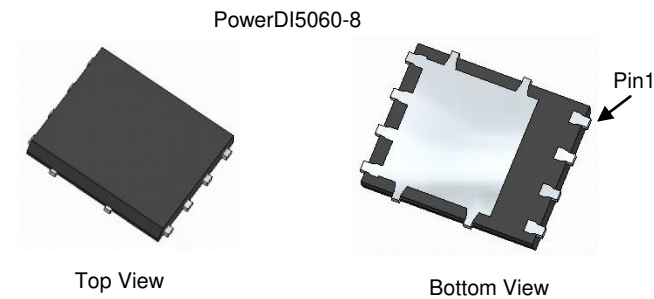
- Notebook Battery Power Management
- DC-DC Converters
- Loadswitch

Features

- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

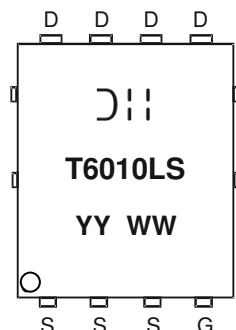


Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6010LPS-13	PowerDI5060-8	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



DII = Manufacturer's Marking
T6010LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5)	I _D	T _A = +25°C	13.5
		T _A = +70°C	11
Continuous Drain Current (Note 6)	I _D	T _C = +25°C (Note 9)	80
		T _C = +70°C	77
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	80	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	125	A
Avalanche Current, L=0.1mH	I _{AS}	20	A
Avalanche Energy, L=0.1mH	E _{AS}	20	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	57	°C/W
Total Power Dissipation (Note 6)	P _D	113	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	1.1	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	µA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	6	8	mΩ	V _{GS} = 10V, I _D = 20A
		-	8	12		V _{GS} = 4.5V, I _D = 20A
Diode Forward Voltage	V _{SD}	-	0.9	1.2	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iSS}	-	2090	-	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	-	746	-		
Reverse Transfer Capacitance	C _{rss}	-	38.5	-		
Gate Resistance	R _g	-	0.59	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	19.3	-	nC	V _{DS} = 30V, I _D = 20A
Total Gate Charge (V _{GS} = 10V)	Q _g	-	41.3	-		
Gate-Source Charge	Q _{gs}	-	6.0	-		
Gate-Drain Charge	Q _{gd}	-	8.8	-		
Turn-On Delay Time	t _{D(ON)}	-	5.7	-	ns	V _{DD} = 30V, V _{GS} = 10V, I _D = 20A, R _G = 3Ω
Turn-On Rise Time	t _R	-	4.3	-		
Turn-Off Delay Time	t _{D(OFF)}	-	23.4	-		
Turn-Off Fall Time	t _F	-	9.7	-		
Body Diode Reverse Recovery Time	t _{RR}	-	35.4	-	ns	I _F = 20A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	-	38.2	-	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.
 - Package limited.

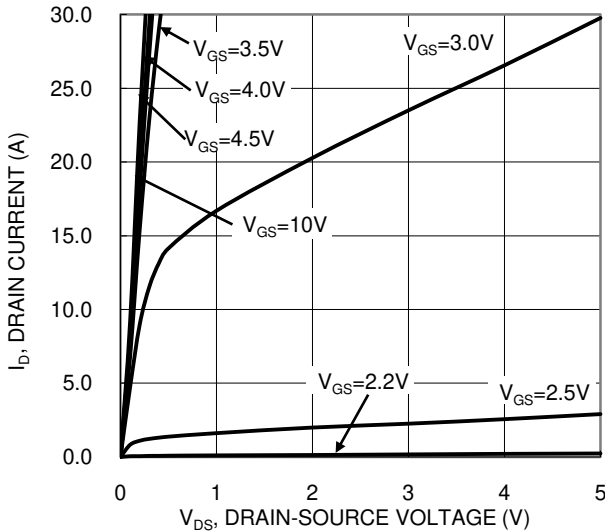


Figure 1. Typical Output Characteristic

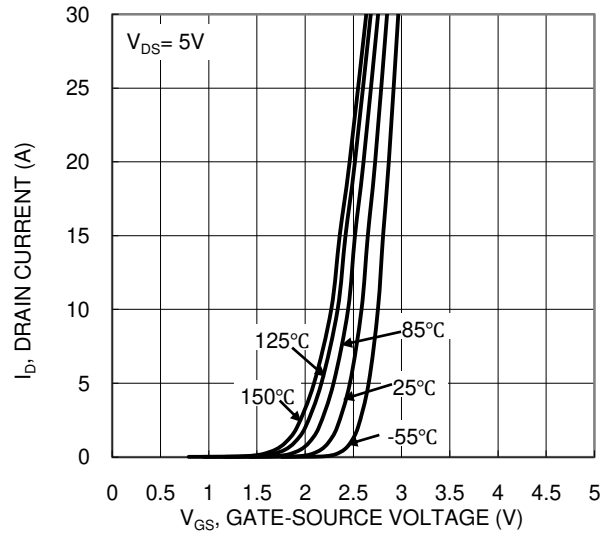


Figure 2. Typical Transfer Characteristic

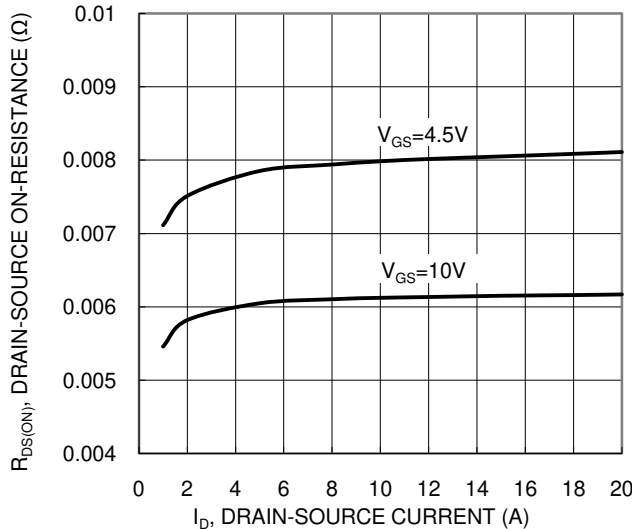


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

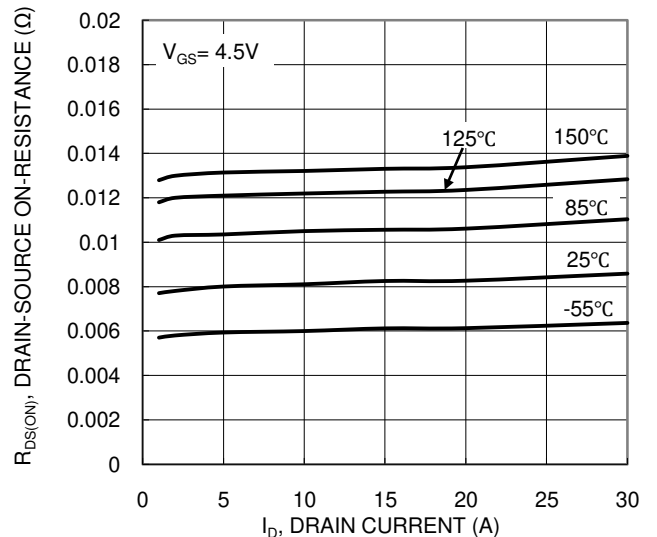


Figure 4. Typical On-Resistance vs. Drain Current and Temperature

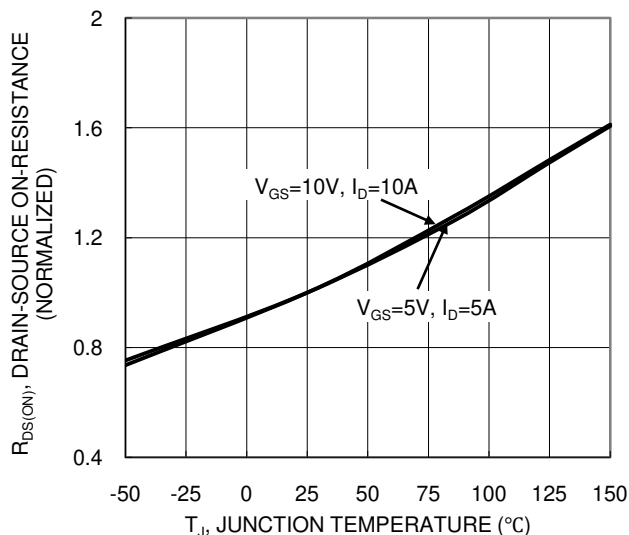


Figure 5. On-Resistance Variation with Temperature

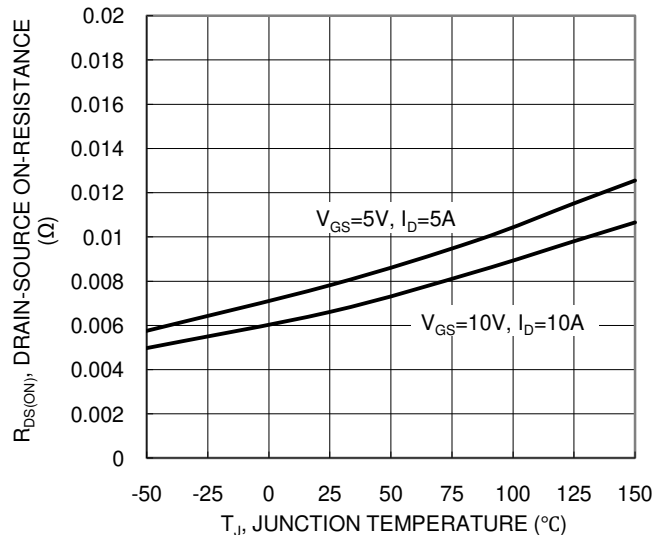


Figure 6. On-Resistance Variation with Temperature

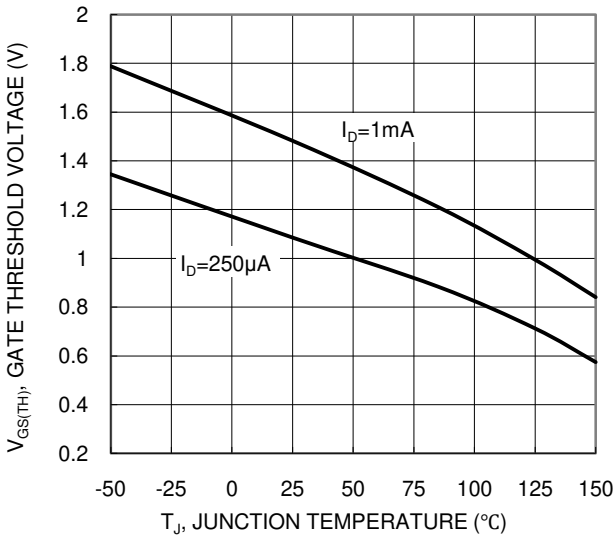


Figure 7. Gate Threshold Variation vs. Junction Temperature

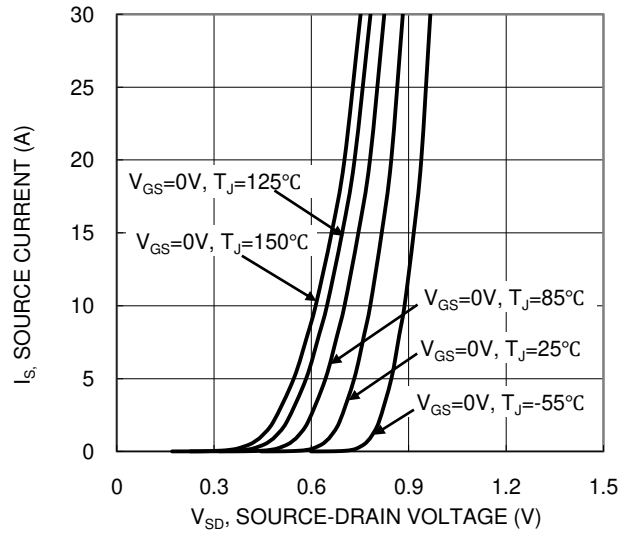


Figure 8. Diode Forward Voltage vs. Current

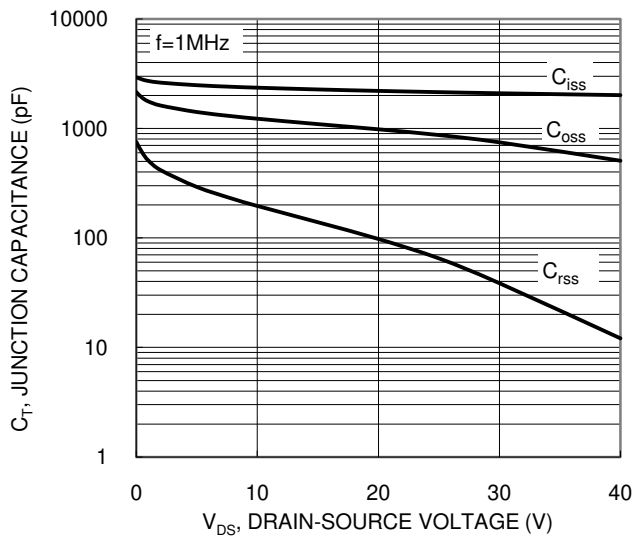


Figure 9. Typical Junction Capacitance

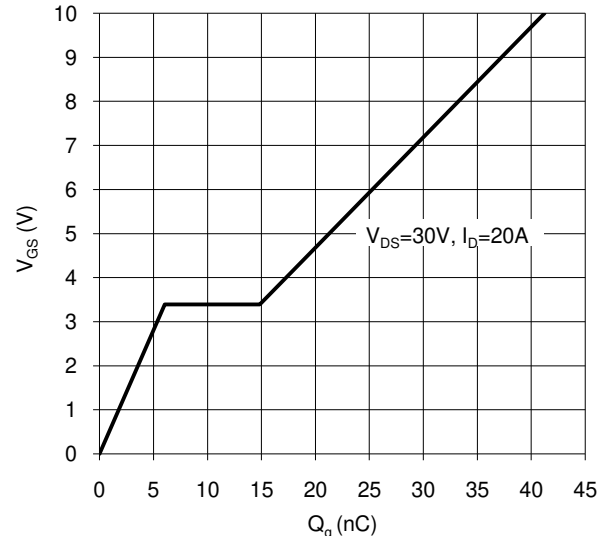


Figure 10. Gate Charge

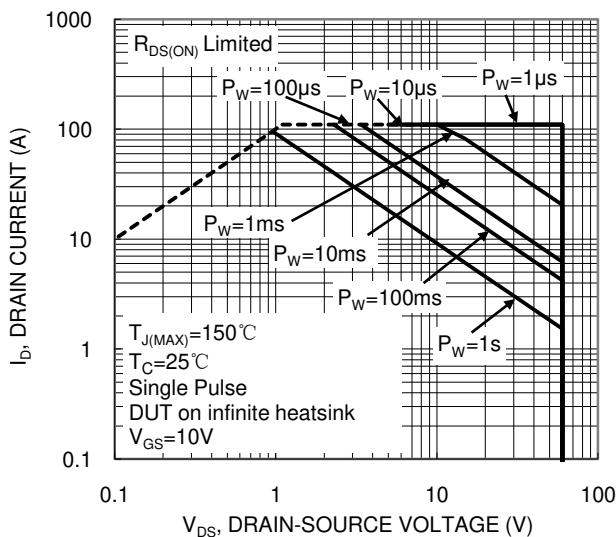


Figure 11. SOA, Safe Operation Area

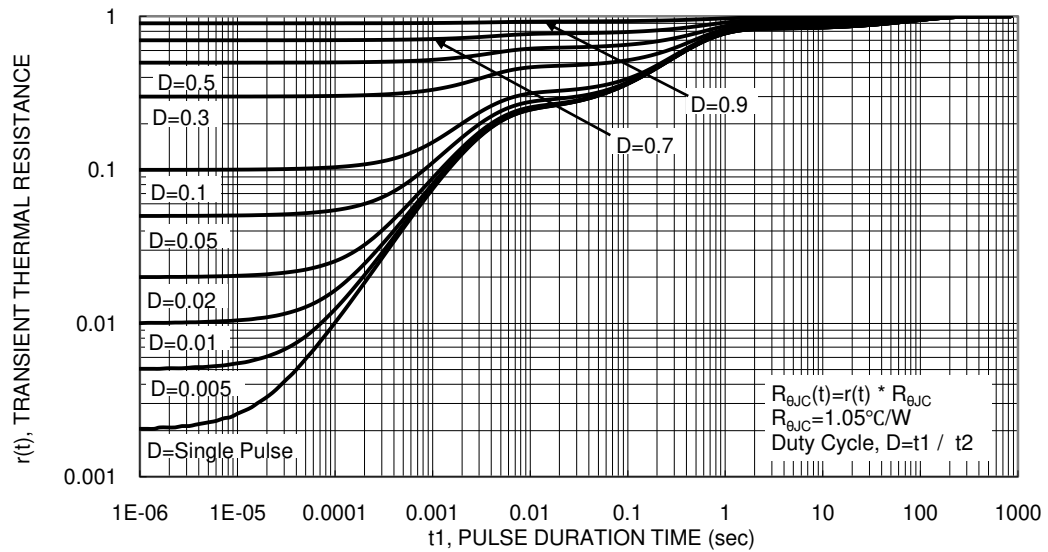
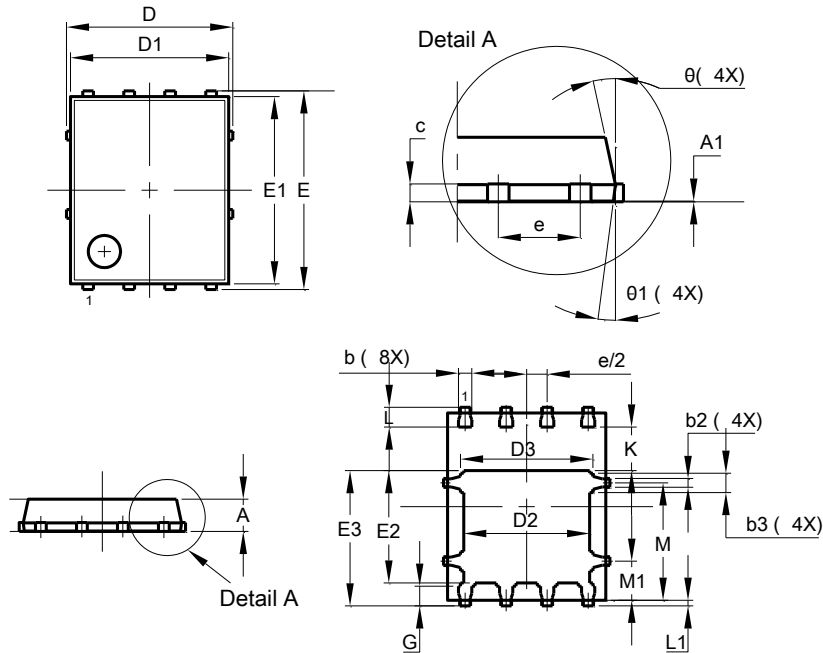


Figure 12. Transient Thermal Resistance

Package Outline Dimensions

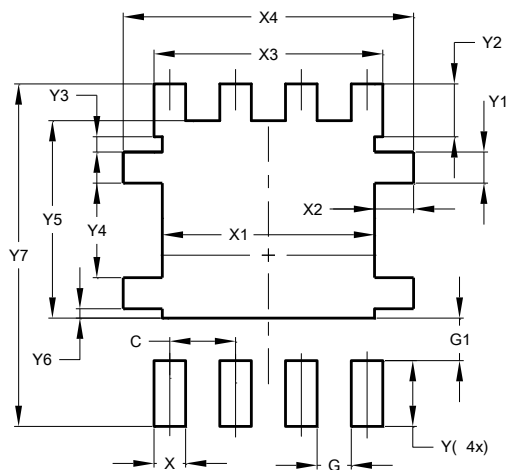
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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